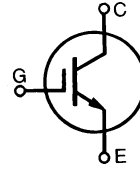


Low $V_{CE(sat)}$ IGBT High speed IGBT

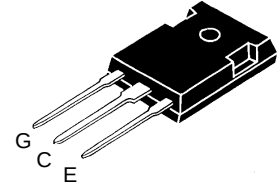
IXGH 10 N100
IXGH 10 N100A

V_{CES}	I_{C25}	$V_{CE(sat)}$
1000 V	20 A	3.5 V
1000 V	20 A	4.0 V



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 1\text{ M}\Omega$	1000	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	20	A
I_{C90}	$T_C = 90^\circ\text{C}$	10	A
I_{CM}	$T_C = 25^\circ\text{C}$, 1 ms	40	A
SSOA (RBSOA)	$V_{GE} = 15\text{ V}$, $T_{VJ} = 125^\circ\text{C}$, $R_G = 150\text{ }\Omega$ Clamped inductive load, $L = 300\text{ }\mu\text{H}$	$I_{CM} = 20$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	100	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10	Nm/lb.in.
Weight		6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$

TO-247 AD



G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- International standard package JEDEC TO-247 AD
- 2nd generation HDMOS™ process
- Low $V_{CE(sat)}$
 - for low on-state conduction losses
- High current handling capability
- MOS Gate turn-on
 - drive simplicity
- Voltage rating guaranteed at high temperature (125°C)

Applications

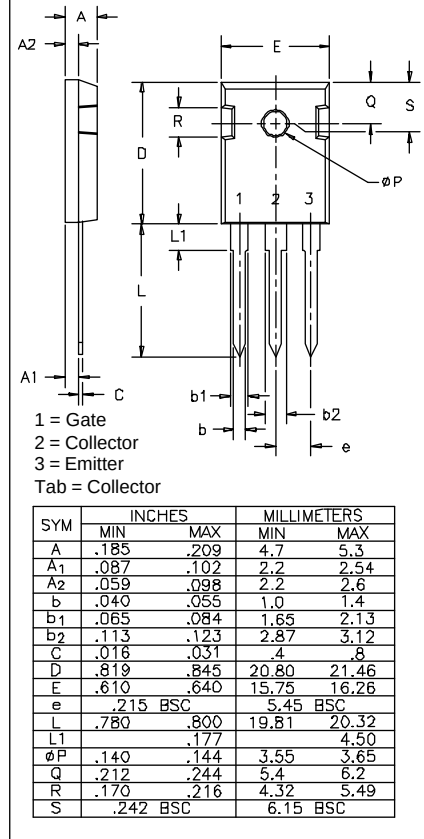
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Advantages

- Easy to mount with 1 screw (isolated mounting screw hole)
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 3\text{ mA}$, $V_{GE} = 0\text{ V}$	1000		V
$V_{GE(th)}$	$I_C = 250\text{ }\mu\text{A}$, $V_{CE} = V_{GE}$	2.5		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0\text{ V}$			250 μA 1 mA
I_{GES}	$V_{CE} = 0\text{ V}$, $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$			3.5 V 4.0 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}$; $V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	4	8	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		750	pF
C_{oes}			150	pF
C_{res}			30	pF
Q_g	$I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		52	nC
Q_{ge}			13	nC
Q_{gc}			24	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 150\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
$t_{d(off)}$			550	ns
t_{fi}		10N100	800	ns
t_{fi}		10N100A	500	ns
E_{off}		10N100A	2	3 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}$, $V_{GE} = 15\text{ V}$, $L = 300\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}$, $R_G = R_{off} = 150\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, higher T_J or increased R_G		100	ns
t_{ri}			200	ns
E_{on}			1.1	mJ
$t_{d(off)}$			600	ns
t_{fi}		10N100	1250	ns
t_{fi}		10N100A	950	ns
E_{off}		10N100	5.0	mJ
E_{off}		10N100A	2.5	mJ
R_{thJC}				1.2 K/W
R_{thCK}			0.25	K/W

TO-247 AD Outline


IXGH 10N100 and IXGH 10N100A characteristic curves are located on the IXGH 10N100U1 and IXGH 10N100AU1 data sheets.